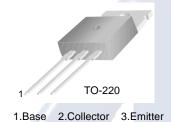


KSA940

Vertical Deflection Output Power Amplifier

• Complement to KSC2073



PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25$ °C unless otherwise noted

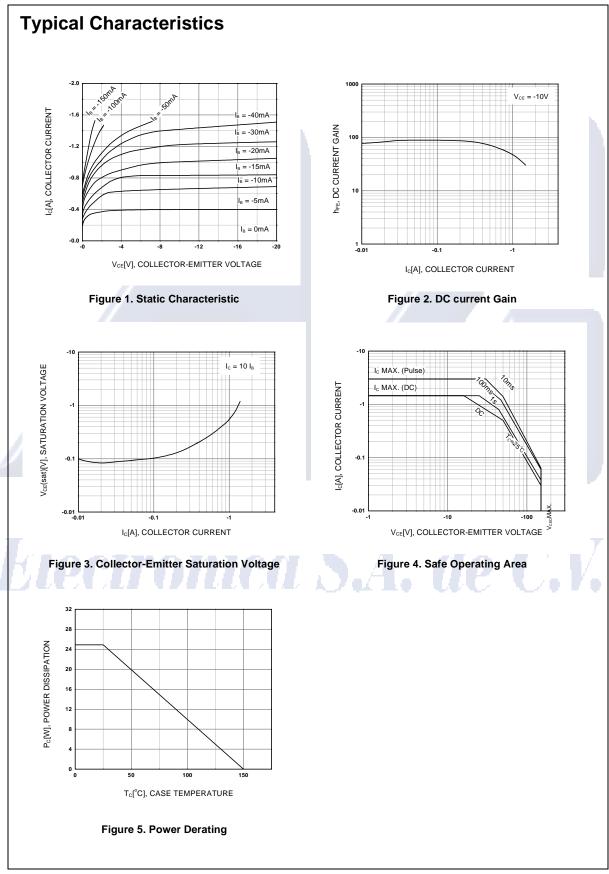
Symbol	Parameter	Ratings	Units
V _{CBO}	Collector-Base Voltage	- 150	V
V _{CEO}	Collector-Emitter Voltage	- 150	V
V _{EBO}	Emitter-Base Voltage	- 5	V
Ic	Collector Current	- 1.5	А
I _B	Base Current	- 0.5	Α
P _C	Collector Dissipation (T _a =25°C)	1.5	W
P _C	Collector Dissipation (T _C =25°C)	25	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I _{CBO}	Collector Cut-off Current	$V_{CB} = -120V, I_{E} = 0$			- 10	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$		n	- 10	μΑ
h _{FE}	DC Current Gain	$V_{CE} = -10V, I_{C} = -500mA$	40	75	140	. 7
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = - 500mA, I _B = - 50mA			- 1.5	V
V _{BE} (on)	Base-Emitter ON Voltage	$V_{CE} = -10V, I_{C} = -500mA$	- 0.65	- 0.75	- 0.85	V
f _T	Current Gain Bandwidth Product	$V_{CE} = -10V, I_{C} = -500mA$		4		MHz
C _{ob}	Output Capacitance	V _{CB} = - 10V, I _E = 0 f = 1MHz		55		pF

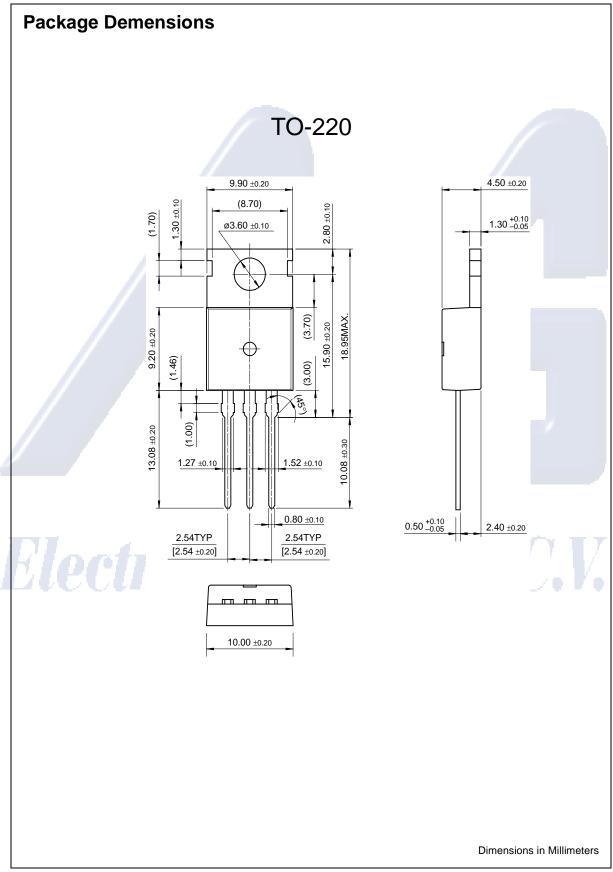
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Definition of Terms

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